

Replaced by  
ART 34 ANDT

## Claims

1. Bipolar transistor, comprising  
an emitter area which can be contacted electrically via an  
5 emitter electrode;  
a base area which can be contacted electrically via a base  
electrode;  
a collector area which can be contacted electrically via a  
collector electrode;
- 10 wherein at least one electrode of the emitter, base and  
collector electrodes is a polysilicon layer, into which  
doping is inserted, and wherein into the at least one  
electrode, in addition to the doping, impurity atoms with a  
density of  $10^{19} - 10^{21} \text{ cm}^{-3}$  are inserted, the impurity atoms  
15 being C, P or Ar atoms.
2. Bipolar transistor according to Claim 1,  
wherein the polysilicon layer is doped with boron atoms.
- 20 3. Bipolar transistor according to Claim 2,  
wherein the concentration of the boron atoms is chosen to  
be greater than  $5 \times 10^{20} \text{ cm}^{-3}$ .
4. Bipolar transistor according to Claim 1,  
25 wherein the at least one electrode consists of  
polycrystalline silicon-germanium.
5. Bipolar transistor according to Claim 1,  
wherein the at least one electrode is the base electrode.
- 30 6. Bipolar transistor according to Claim 1,  
wherein the bipolar transistor is a self-aligned bipolar  
transistor.